

L7 ANSWER 6 OF 18 HCAPLUS COPYRIGHT 2003 ACS on STN
 AN 2001:225711 HCAPLUS

DN 134:260170
 TI Formation of dielectric layer of capacitor
 IN Fuang, Guo Tai; You, Cui Rong
 PA Lien Hua Electronics Co., Ltd., Taiwan
 SO Jpn. Kokai Tokkyo Koho, 6 pp.
 CODEN: JKXXAF

DT Patent

LA Japanese

IC ICM H01L021-316
 ICS C23C016-40; H01L021-31; H01L027-108; H01L021-8242; H01G004-33;
 H01G004-10

CC 76-10 (Electric Phenomena)
 Section cross-reference(s): 75

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI JP 2001085423	A2	20010330	JP 1999-256379	19990909

PRAI JP 1999-256379 19990909
 AB The title method involves prepg. an org. compd. contg. Ta and an org. compd. contg. Ti, and carrying out MOCVD using the org. compds. as precursors. A dielec. layer of tantalum titanium oxide having a high dielec. const. is formed. A method is also described, for forming a capacitor of a DRAM using the above method.

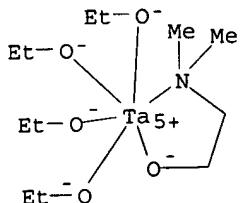
IT 172901-22-3 177580-52-8 177580-53-9

238757-13-6

RL: NUU (Other use, unclassified); USES (Uses)
 (MOCVD of tantalum titanium oxide dielec. layer of capacitor)

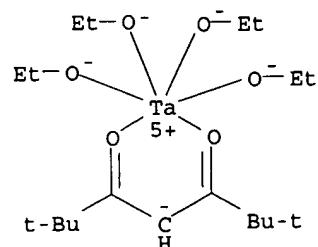
RN 172901-22-3 HCAPLUS

CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)



RN 177580-52-8 HCAPLUS

CN Tantalum, tetraethoxy(2,2,6,6-tetramethyl-3,5-heptanedionato-.kappa.O,.kappa.O')-, (OC-6-22)- (9CI) (CA INDEX NAME)



RN 177580-53-9 HCAPLUS

CN Tantalum, tetrakis(2-propanolato)(2,2,6,6-tetramethyl-3,5-heptanedionato-.kappa.O,.kappa.O')-, (OC-6-22)- (9CI) (CA INDEX NAME)

priority date = 9/9/99
 JP pub.date = 3/30/01

Might be
 too new date.